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JP-A 2062077; JP-A 63213311; JP-A 88213311

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PATENT ABSTRACTS OF JAPAN

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March 1, 1990

THIN FILM TRANSISTOR

INVENTOR: MISHIMA YASUYOSHI; MATSUMOTO TOMOTAKA; KIMURA TADAYUKI

APPL-NO: 63213311 (JP 88213311)

FILED: August 26, 1988

ASSIGNEE: FUJITSU LTD

INT-CL: H01L29/784, (Section H, Class 01, Sub-class L, Group 29, Sub-group 784);
G02F1/136, (Section G, Class 02, Sub-class F, Group 1, Sub-group 136)

ABST:

PURPOSE: To improve a characteristic and uniformity by making a operating semiconductor layer of a thin film transistor double-layered, while an electric characteristic is mainly held by a first layer and a second layer plays an auxiliary role.

CONSTITUTION: A gate electrode 2 is formed on a transparent insulating substrate 1 while forming a gate electrode 3. An operating semiconductor layer 4 is made a double-layer construction of a non-doped a-Si layer 4a connecting to the gate insulating film 3 and of a second semiconductor layer 4b having a band gap larger than a-Si, accordingly lower photosensitivity to white light than a-Si such as an a-Si[1-x]C[x] layer (carbon-doped amorphous silicon) layer and an a-Si[1-x]N[x] (nitrogen amorphous silicon) layer. The film thickness of the layer 4a is made thin less than 300 [angstrom] for making a photocurrent, while the film thickness of the layer 4b is made sufficiently thicker than that of the layer 4a in order to form both together of the required film thickness as the operating semiconductor layer 4. Accordingly, photoabsorption can be made extremely little.

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